

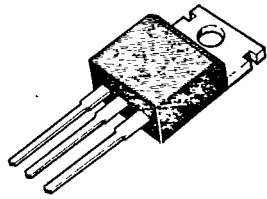
**SEMELAB**

T-33-09

JUN 29 1987  
SMLB

*In*  
**BUP34**

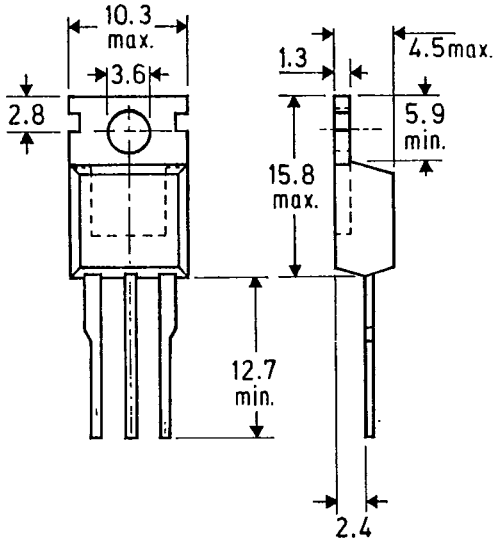
**NEW PRODUCT**



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**MECHANICAL DATA**

**SILICON NPN  
EPITAXIAL PLANAR**



**FEATURES**

- Very high breakdown voltage
- Low  $C_{ob}$
- Very fast switching
- High reliability

TO-220

**ABSOLUTE MAXIMUM RATINGS AT 25°C**

VCBO	1500	Volts
VCEO	900	Volts
VEBO	5	Volts
$I_C$ PK	1	Amps
$P_T$	20	Watts
$T_j$	150	°C
$T_{stg}$	-55 + 150	°C

8001-0115 Editor *Handwritten signature*

MARCH 1986

**CHARACTERISTICS AT 25°C**

		MIN.	TYP.	MAX.	UNITS
$I_{CBO}$	$V_{CBO} = 900$ Volts			10	Micro Amps
$I_{EBO}$	$V_{EB} = 4$ Volts			10	Micro Amps
$h_{FE1}$	$I_C = 1$ mA $V_{CE} = 5$ Volts	30	50		
$h_{FE2}$	$I_C = 50$ mA $V_{CE} = 5$ Volts	30	50		
$V_{CE} (sat)$	$I_C = 60$ mA $I_B = 6$ mA			2	Volts
$V_{BE} (sat)$	$I_C = 60$ mA $I_B = 6$ mA			2	Volts
$f_T$	$I_C = 30$ mA $V_{CE} = 5$ Volts		6		MHz
$C_{ob}$	$V_{CB} = 100$ Volts $f = 1$ MHz		5		pf
$I_{SB1}$	$V_{CE} = 500$ Volts $t = 1$ m sec	30			Milli Amps